

SavantIC Semiconductor

Product Specification

Silicon PNP Power Transistors

2N3791 2N3792

DESCRIPTION

- With TO-3 package
- Complement to type 2N3715 ,2N3716
- Excellent safe operating area

APPLICATIONS

Designed for medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

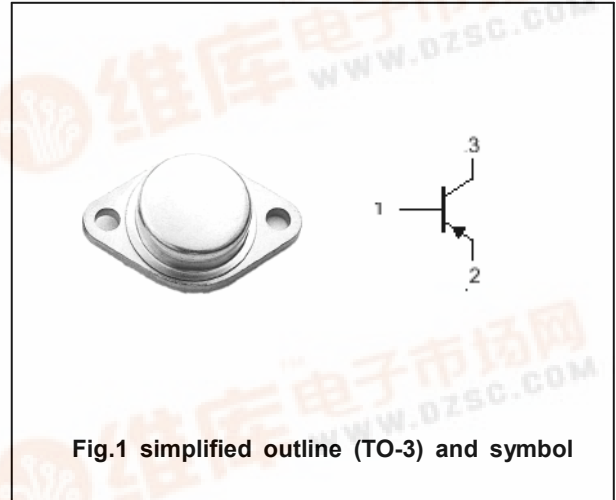


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N3791	-60	V
		2N3792	-80	
V _{CEO}	Collector-emitter voltage	2N3791	-60	V
		2N3792	-80	
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-10	A
I _B	Base current		-4	A
P _D	Total Power Dissipation	T _c =25°C	150	W
T _j	Junction temperature		200	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{(th) jc}	Thermal resistance junction to case	1.17	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N3791	I _C =-0.2A ; I _B =0			V	
		2N3792		-60		V	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.0	V	
V _{BE(on)-1}	Base-emitter on voltage	I _C =-5A ; V _{CE} =-2V			-1.8	V	
V _{BE(on)-2}	Base-emitter on voltage	I _C =-10A ; V _{CE} =-4V			-4.0	V	
I _{C EX}	Collector cut-off current	2N3791	V _{CE} =-60V; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -5.0	mA
		2N3792		V _{CE} =-80V; V _{BE(off)} =-1.5V T _C =150°C			-1.0 -5.0
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-5.0	mA	
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-2V	50		180		
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-2V	30				
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-10V	4			MHz	

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PACKAGE OUTLINE

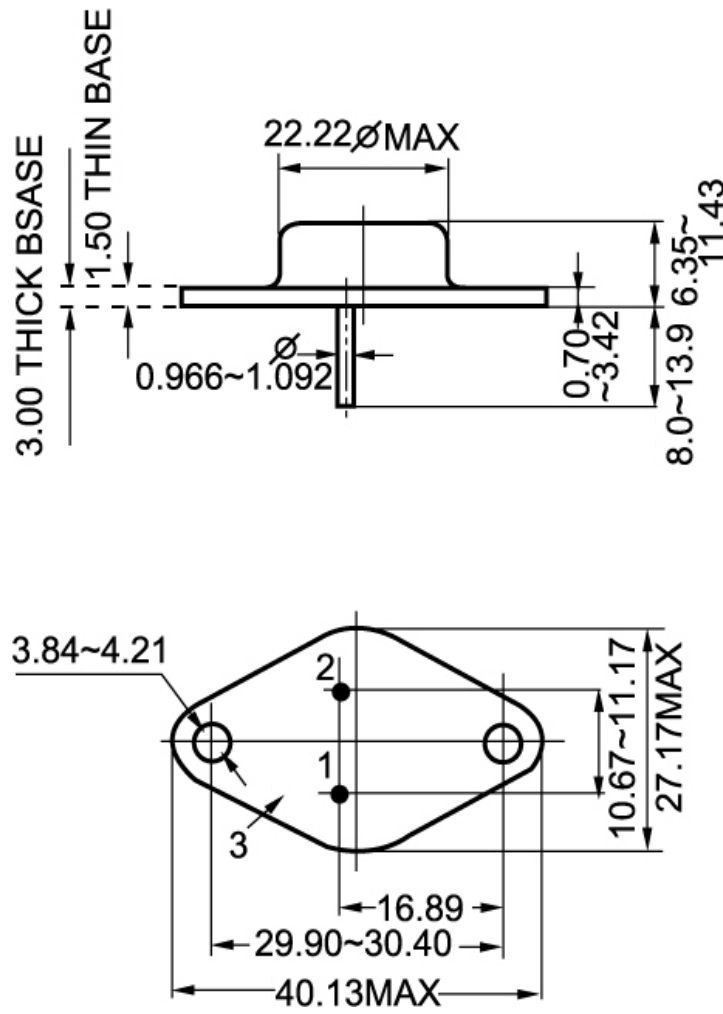


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)